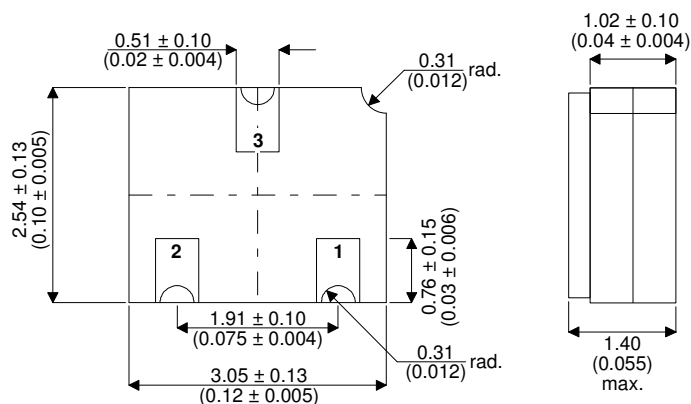


MECHANICAL DATA

Dimensions in mm (inches)



LCC1 PACKAGE

Pad 1 - Base Pad 2 - Emitter Pad 3 - Collector

HIGH SPEED MEDIUM POWER PNP SWITCHING TRANSISTOR

FEATURES

- SILICON PNP TRANSISTOR.
- HIGH SPEED SWITCHING
- SCREENING OPTIONS AVAILABLE

APPLICATIONS

- SMALL SIGNAL GENERAL PURPOSE AND SWITCHING APPLICATIONS

ABSOLUTE MAXIMUM RATINGS

$T_{CASE} = 25^{\circ}\text{C}$ unless otherwise stated

V_{CBO}	Collector - Base Voltage	50V
V_{CEO}	Collector - Emitter Voltage ($I_B = 0$)	40V
V_{EBO}	Emitter - Base Voltage ($I_C = 0$)	5V
I_C	Continuous Collector Current	600mA
P_D	Total Power Dissipation at $T_{Amb} = 25^{\circ}\text{C}$ Derate Above 25°C	400mW 2.7mW/ $^{\circ}\text{C}$
T_{stg}, T_J	Operating and Storage Temperature Range	-55 to $+175^{\circ}\text{C}$

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THERMAL CHARACTERISTICS

	Max.	Unit
$R_{th j-Amb}$ Thermal resistance to ambient	375	°C/W

ELECTRICAL CHARACTERISTICS ($T_{Amb} = 25^{\circ}C$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CBO}^*$ Collector-Base Breakdown Voltage	$I_C = 10\mu A$ $I_E = 0$	50			V
$V_{(BR)CEO}^*$ Collector-Emitter Breakdown Voltage	$I_C = 10mA$ $I_B = 0$	40			
I_{CBO} Collector to Base Cut-Off Current	$I_E = 0$ $V_{CB} = 50V$			10	μA
	$I_E = 0$ $V_{CB} = 30V$			1	
	$I_E = 0$ $T_{amb} = 150^{\circ}C$			100	
I_{EBO} Emitter to Base Cut-Off Current	$I_C = 0$ $V_{EB} = 5V$			100	
I_{CER} Collector to Emitter Cut-Off Current	$R_{BE} \leq 10\Omega$ $V_{CE} = 50V$			10	mA
h_{FE}^* DC Current Gain	$V_{CE} = 10V$	$I_C = 150mA$	30	100	
		$I_C = 5mA$	25		
$V_{CE(SAT)}^*$ Collector To Emitter Saturation Voltage	$I_C = 150mA$ $I_B = 15mA$			1.3	V
$V_{BE(SAT)}^*$ Base To Emitter Saturation Voltage				1.5	

DYNAMIC CHARACTERISTICS

C_{OBO} Output Capacitance	$V_{CB} = 10V$ $I_E = 0$ $f = 1.0MHz$			45	pF
C_{IBO} Input Capacitance	$V_{EB} = 0.5V$ $I_C = 0$ $f = 1.0MHz$			80	
$ h_{fe} $ Small Signal Current Gain	$I_C = 50mA$ $V_{CE} = 10V$ $f = 20MHz$	3.0		20	
t_d Delay Time	$V_{CC} = 30V$ $I_C = 150mA$ $I_{B1} - I_{B2} = 15mA$			15	nS
t_r Rise Time				25	
t_s Storage Time				80	
t_f Fall Time				25	

* Pulse test $t_p = 300\mu s$, $\delta < 2\%$

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